

SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 8, line 20 with:

B¹ Reference numeral 12 designates an InP substrate of p-conductivity type serving as a semiconductor substrate (hereinafter a p-conductivity type is simply expressed as "p-" and an n-conductivity type is expressed as "n-"); 14 designates a lower p-InP cladding layer which is laid on the p-InP substrate 12 and acts as a first cladding layer; and 16 designates an active layer of InGaAsP-based material laid on the lower cladding layer 14. For instance, the active layer is a multiple quantum structure active layer comprising, e.g., five to fifteen quantum well layers. Upper and lower surfaces of the active layer 16 are ~~formed to be~~ uniformly flat in the direction of the optical waveguide. The active layer 16 ~~has~~ does not have the function of a diffraction grating.

Replace the paragraph beginning at page 15, line 28 with:

B² $\lambda_p - 1000 \text{ } \underline{100} \text{ nm} \leq \lambda_g \leq \lambda_p + 100 \text{ nm} \dots (4)$